Cheng-Wei Cheng

List of Publications by Year
in descending order

10	187	1163117 8	1372567 10
papers	citations	h-index	g-index

10	10	10	294
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	The effect of interface processing on the distribution of interfacial defect states and the C-V characteristics of III-V metal-oxide-semiconductor field effect transistors. Journal of Applied Physics, 2011, 109, 023714.	2.5	52
2	In situ metal-organic chemical vapor deposition atomic-layer deposition of aluminum oxide on GaAs using trimethyaluminum and isopropanol precursors. Applied Physics Letters, 2008, 93, .	3.3	44
3	Self-cleaning and surface recovery with arsine pretreatment in ex situ atomic-layer-deposition of Al2O3 on GaAs. Applied Physics Letters, 2009, 95, .	3.3	27
4	Nanocomposite membranes of polybenzimidazole and amine-functionalized carbon nanofibers for high temperature proton exchange membrane fuel cells. RSC Advances, 2021, 11, 9964-9976.	3.6	14
5	Enhanced Polarization Switching Characteristics of Pb(Zr0.5Ti0.5)O3â€“Pt Nanocomposite Thin Films. Journal of Materials Research, 2004, 19, 1043-1049.	2.6	12
6	High mobility In0.53Ga0.47As quantum-well metal oxide semiconductor field effect transistor structures. Journal of Applied Physics, 2012, 111, 104511.	2.5	12
7	Dimethylimidazolium-Functionalized Polybenzimidazole and Its Organicâ€“Inorganic Hybrid Membranes for Anion Exchange Membrane Fuel Cells. Polymers, 2021, 13, 2864.	4.5	10
8	Improved interfacial state density in Al2O3/GaAs interfaces using metal-organic chemical vapor deposition. Applied Physics Letters, 2010, 96, .	3.3	9
9	Field enhancement effect of nanocrystals in bandgap engineering of tunnel oxide for nonvolatile memory application. Applied Physics Letters, 2009, 94, 082901.	3.3	5
10	(Invited) Effect of Al₂O₃/InGaAs Interface on Channel Mobility. ECS Transactions, 2011, 41, 219-225.	0.5	2